

Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.8)	V_{pp}	2.5	kV
--	----------	-----	----

ELECTRICAL CHARACTERISTICS (unless otherwise specified)

Symbol	Test Condition	Quadrant	Value	Unit	
I	V _G =12V R _L =33	- -	MAX.	50	mA
V		- -	MAX.	1.3	V
V	V _G =V _{DRM} T _j =125 R _L =3.3k	- -	MIN.	0.15	V
I _L	I _G =1.2I _{GT}	-	MAX.	80	mA
				100	
I _H	I _T =500mA		MAX.	75	mA
dV/dt	V _D =540V Gate Open T _j =125		MIN.	2000	V / s
(dI/dt) _c	G 9 G W F j=125 V 7		MIN.	25	A/ms
t _{on}	I _G =80mA I _A =400mA I _R =40mA T _j =25		TYP.	10	s
t _{off}				70	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX .)	Unit
V _{TM}	I _{TM} =42A t _p =380 s	T _j =25	1.5	V
V _{TO}	Threshold voltage	T _j =125	0.72	V
R _D	Dynamic resistance	T _j =125	25	m
I _{DRM}	V _D =V _{DRM} V _R =V _{RRM}	T _j =25	5	A
I _{RRM}		T _j =125	2	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	0.7	/W
$R_{th(j-a)}$	junction to ambient (AC, in free air, $S=2cm^2$)	45	/W

ORDERING INFORMATION

J	ST	30	E	-800	BW	-/
JieJie Microelectronics Co., Ltd.	Triacs	$I_T(RMS):30A$				Blank:Tube -TR:Tape & Reel
			$E:TO-263$		$BW:I_{GT1-3} \leq 50mA$	
				$800:V_{DRM} / V_{RRM} \geq 800V$		

MARKING

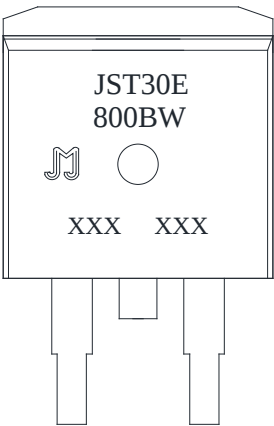


FIG.1: Maximum power dissipation versus RMS
on-state current

FIG.2: RMS on-state current versus case
temperature

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

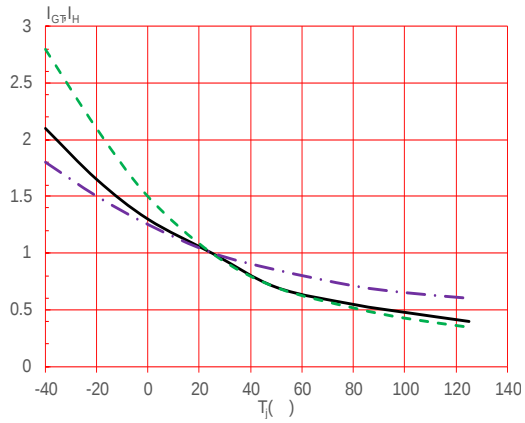
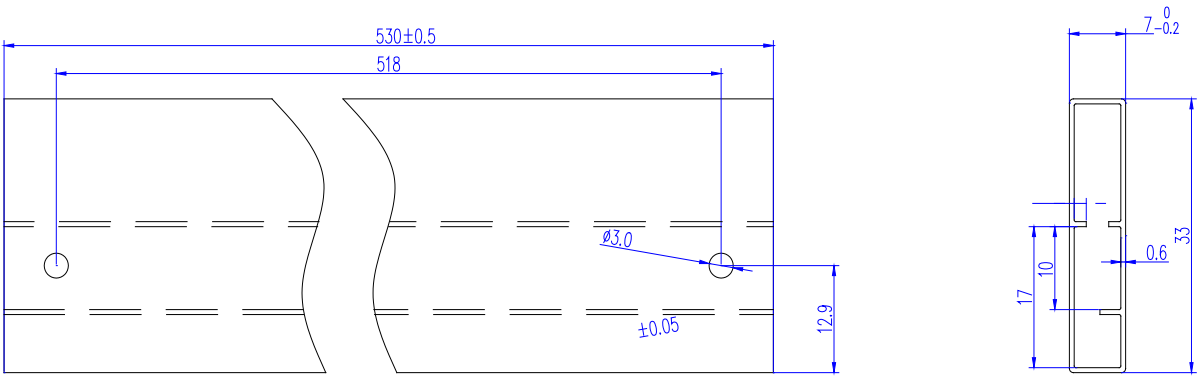


FIG.8: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



DELIVERY MODE



Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co., Ltd. assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Jiangsu JieJie complies with the agreement.

Products and information provided in this document have no infringement of patents. Jiangsu JieJie assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information. This document supersedes and replaces all information previously supplied.



is a registered trademark of Jiangsu JieJie Microelectronics Co., Ltd.

Copyright © 2025 Jiangsu JieJie Microelectronics Co., Ltd. All rights reserved.